

ABSTRACT

According to one embodiment, a memory device includes:
a first semiconductor layer, a first conductive layer, a
second semiconductor layer, and a second conductive layer
5 that are arranged in this order in a first direction,
spaced apart from each other; a first semiconductor film
extending in the first direction, being in contact with the
first semiconductor layer and the second semiconductor
layer, and intersecting the first conductive layer and the
10 second conductive layer; a first memory film provided
between the first conductive layer and the first
semiconductor film; and a second memory film provided
between the second conductive layer and the first
semiconductor film.